

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

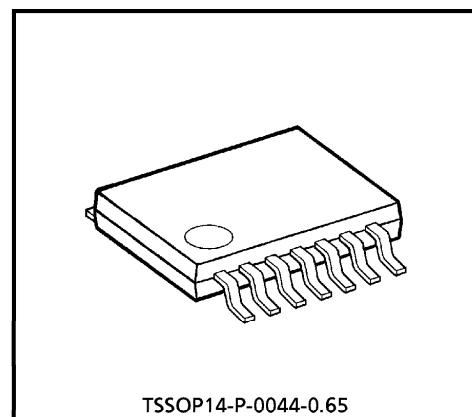
TC74VCX00FT

LOW-VOLTAGE QUAD 2-INPUT NAND GATE WITH 3.6 V TOLERANT INPUTS AND OUTPUTS

The TC74VCX00FT is a high performance CMOS 2-INPUT NAND GATE. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation. It is also designed with over voltage tolerant inputs and outputs up to 3.6 V. All inputs are equipped with protection circuits against static discharge.

FEATURES

- Low Voltage Operation : $V_{CC} = 1.8\sim 3.6\text{ V}$
- High Speed Operation : $t_{pd} = 2.8\text{ ns (max) at } V_{CC} = 3.0\sim 3.6\text{ V}$
 $t_{pd} = 3.7\text{ ns (max) at } V_{CC} = 2.3\sim 2.7\text{ V}$
 $t_{pd} = 7.4\text{ ns (max) at } V_{CC} = 1.8\text{ V}$
- Output Current : $I_{OH}/I_{OL} = \pm 24\text{ mA (min) at } V_{CC} = 3.0\text{ V}$
 $I_{OH}/I_{OL} = \pm 18\text{ mA (min) at } V_{CC} = 2.3\text{ V}$
 $I_{OH}/I_{OL} = \pm 6\text{ mA (min) at } V_{CC} = 1.8\text{ V}$
- Latch-up Performance : $\pm 300\text{ mA}$
- ESD Performance : Human Body Model $> \pm 2000\text{ V}$
Machine Model $> \pm 200\text{ V}$
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.

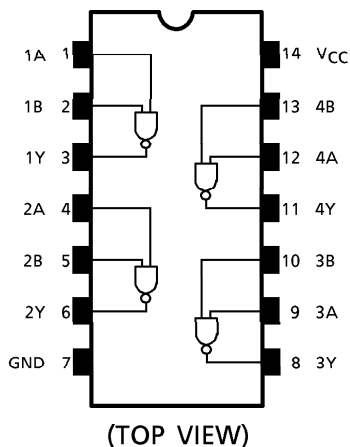


Weight : 0.06 g (Typ.)

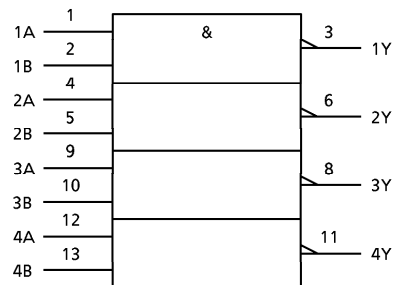
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PIN CONNECTION



IEC LOGIC SYMBOL



TRUTH TABLE

INPUTS		OUTPUTS
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~4.6	V
DC Input Voltage	V_{IN}	-0.5~4.6	V
DC Output Voltage	V_{OUT}	-0.5~4.6 (Note 1)	V
		-0.5~ $V_{CC} + 0.5$ (Note 2)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	180	mW
DC V_{CC} /Ground Current	I_{CC}/I_{GND}	±100	mA
Storage Temperature	T_{stg}	-65~150	°C

(Note 1): $V_{CC} = 0\text{ V}$

(Note 2): High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3): $V_{OUT} < GND, V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V _{IN}	-0.3~3.6	V
Output Voltage	V _{OUT}	0~3.6 (Note 5)	V
		0~V _{CC} (Note 6)	
Output Current	I _{OH} / I _{OL}	±24 (Note 7)	mA
		±18 (Note 8)	
		±6 (Note 9)	
Operating Temperature	T _{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns/V

(Note 4): Data Retention Only

(Note 5): V_{CC} = 0 V

(Note 6): High or Low State

(Note 7): V_{CC} = 3.0~3.6 V

(Note 8): V_{CC} = 2.3~2.7 V

(Note 9): V_{CC} = 1.8 V

(Note 10): V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.7 V < V_{CC} ≤ 3.6 V)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN	MAX	UNIT		
Input Voltage	"H" Level	V _{IH}	2.7~3.6	2.0	—	V		
	"L" Level	V _{IL}	2.7~3.6	—	0.8			
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12 mA	2.7	2.2	—	
				I _{OH} = -18 mA	3.0	2.4	—	
				I _{OH} = -24 mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 100 μA	2.7~3.6	—	0.2	
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 18 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input Leakage Current	I _{IN}	V _{IN} = 0~3.6 V	2.7~3.6	—	±5.0	μA		
Power Off Leakage Current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V	0	—	10.0	μA		
Quiescent Supply Current	I _{CC}	V _{IN} = V _{CC} or GND	2.7~3.6	—	20.0	μA		
		V _{CC} ≤ V _{IN} ≤ 3.6 V	2.7~3.6	—	±20.0			
Increase In I _{CC} Per Input	ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V	2.7~3.6	—	750	μA		

ELECTRICAL CHARACTERISTICS

DC characteristics ($T_a = -40\sim 85^\circ\text{C}$, $2.3\text{ V} \leq V_{CC} \leq 2.7\text{ V}$)

PARAMETER		SYMBOL	TEST CONDITION	V_{CC} (V)	MIN	MAX	UNIT	
Input Voltage	"H" Level	V_{IH}		2.3~2.7	1.6	—	V	
	"L" Level	V_{IL}		2.3~2.7	—	0.7		
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100\ \mu\text{A}$	2.3~2.7	$V_{CC} - 0.2$	—	V
				$I_{OH} = -6\ \text{mA}$	2.3	2.0	—	
				$I_{OH} = -12\ \text{mA}$	2.3	1.8	—	
				$I_{OH} = -18\ \text{mA}$	2.3	1.7	—	
	"L" Level	V_{OL}	$V_{IN} = V_{IH}$	$I_{OL} = 100\ \mu\text{A}$	2.3~2.7	—	0.2	
				$I_{OL} = 12\ \text{mA}$	2.3	—	0.4	
$I_{OL} = 18\ \text{mA}$				2.3	—	0.6		
Input Leakage Current		I_{IN}	$V_{IN} = 0\sim 3.6\text{ V}$	2.3~2.7	—	± 5.0	μA	
Power Off Leakage Current		I_{OFF}	$V_{IN}, V_{OUT} = 0\sim 3.6\text{ V}$	0	—	10.0	μA	
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC}$ or GND	2.3~2.7	—	20.0	μA	
			$V_{CC} \leq V_{IN} \leq 3.6\text{ V}$	2.3~2.7	—	± 20.0		

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 1.8 V ≤ VCC < 2.3 V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN	MAX	UNIT
					1.8~2.3			
Input Voltage	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}	—	V
	"L" Level	V _{IL}			1.8~2.3	—	0.2 × V _{CC}	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	1.8	1.4	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH}	I _{OL} = 100 μA	1.8	—	0.2	
				I _{OL} = 6 mA	1.8	—	0.3	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6 V		1.8	—	± 5.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ V _{IN} ≤ 3.6 V		1.8	—	± 20.0	

AC characteristics (Ta = -40~85°C, Input t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN	MAX	UNIT
					1.8			
Propagation Delay Time	t _{pLH} t _{pHL}	(Fig.1, 2)			1.8	1.0	7.4	ns
					2.5 ± 0.2	0.8	3.7	
					3.3 ± 0.3	0.6	2.8	
Output To Output Skew	t _{osLH} t _{osHL}	(Note 11)			1.8	—	0.5	ns
					2.5 ± 0.2	—	0.5	
					3.3 ± 0.3	—	0.5	

For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

(Note 11): Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics (Ta = 25°C, Input tr = tf = 2.0 ns, CL = 30 pF)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Quiet Output Maximum Dynamic VOL	VOLP	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	0.25	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	0.6	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	0.8	
Quiet Output Minimum Dynamic VOL	VOLV	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	-0.25	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	-0.6	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	-0.8	
Quiet Output Minimum Dynamic VOH	VOHV	VIH = 1.8 V, VIL = 0 V (Note 12)	1.8	1.5	V
		VIH = 2.5 V, VIL = 0 V (Note 12)	2.5	1.9	
		VIH = 3.3 V, VIL = 0 V (Note 12)	3.3	2.2	

(Note 12): Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Input Capacitance	CIN	—	1.8, 2.5, 3.3	6	pF
Power Dissipation Capacitance	CPD	fIN = 10MHz (Note 13)	1.8, 2.5, 3.3	20	pF

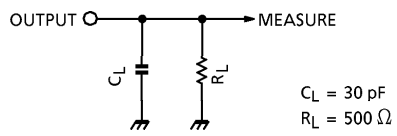
(Note 13): CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \text{ (per gate)}$$

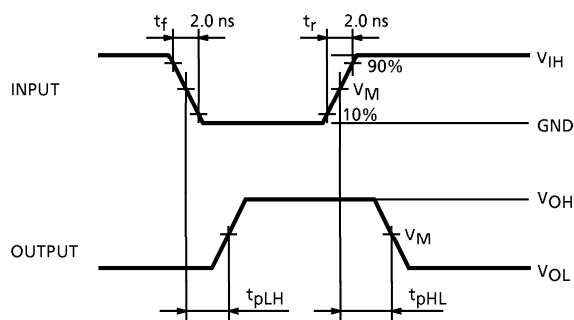
TEST CIRCUIT

Fig.1



AC WAVEFORM

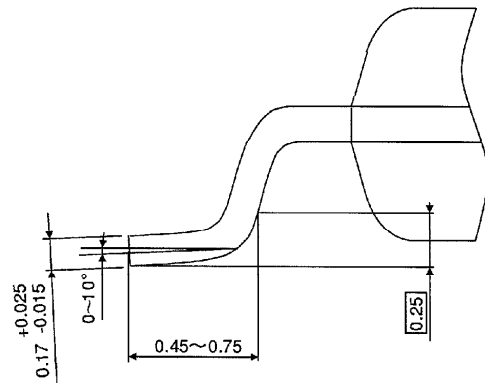
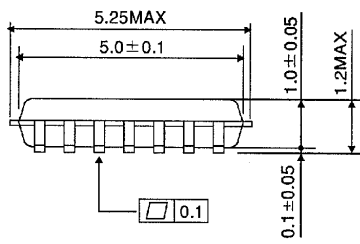
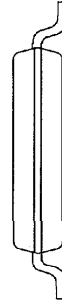
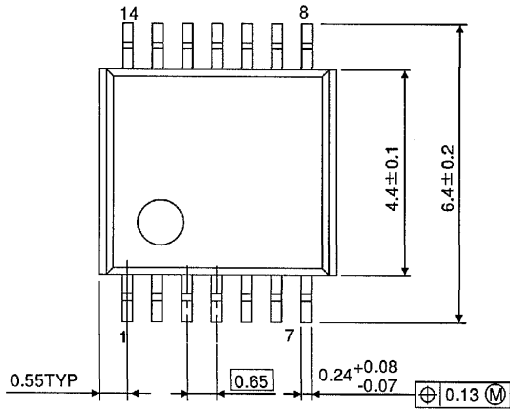
Fig.2 t_{pLH} , t_{pHL}



SYMBOL	V_{CC}		
	$3.3 \pm 0.3 \text{ V}$	$2.5 \pm 0.2 \text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$

OUTLINE DRAWING
TSSOP14-P-0044-0.65

Unit : mm



Weight : 0.06 g (Typ.)